

Oliver Ambacher

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	A Scalable Small-Signal and Noise Model for High-Electron-Mobility Transistors Working Down to Cryogenic Temperatures. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 1097-1110.	4.6	9
2	Manipulation of the In Situ Nitrogen-Vacancy Doping Efficiency in CVD-Grown Diamond. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	1.8	3
3	On the origin of the turn-on voltage drop of GaN-based current aperture vertical electron transistors. Journal of Applied Physics, 2022, 131, .	2.5	3
4	Effect of V/III ratio and growth pressure on surface and crystal quality of AlN grown on sapphire by metal-organic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	2.1	4
5	C-Band Low-Noise Amplifier MMIC with an Average Noise Temperature of 44.5 K and 24.8 mW Power Consumption. , 2022, , .		2
6	Electron accumulation and distribution at interfaces of hexagonal Sc _x Al _{1-x} N/GaN- and Sc _x Al _{1-x} N/InN-heterostructures. Journal of Applied Physics, 2022, 131, .	2.5	7
7	Analysis of the Growth of Laterally Aligned SnO ₂ Nanowires by Thermodynamic Considerations and Experiments. Crystal Growth and Design, 2021, 21, 191-199.	3.0	7
8	Growth and Fabrication of Quasivertical Current Aperture Vertical Electron Transistor Structures. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000379.	1.8	9
9	Monolithic Integrated AlGaN/GaN Power Converter Topologies on High-Voltage AlN/GaN Superlattice Buffer. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000404.	1.8	12
10	Metal organic chemical vapour deposition regrown large area GaN-on-GaN current aperture vertical electron transistors with high current capability. Electronics Letters, 2021, 57, 145-147.	1.0	6
11	Technology of GaN-Based Large Area CAVETs With Co-Integrated HEMTs. IEEE Transactions on Electron Devices, 2021, 68, 5547-5552.	3.0	8
12	Improved AlScN/GaN heterostructures grown by metal-organic chemical vapor deposition. Semiconductor Science and Technology, 2021, 36, 034003.	2.0	34
13	First-principles calculation of electroacoustic properties of wurtzite (Al,Sc)N. Physical Review B, 2021, 103, .	3.2	41
14	Low-Power Differential Input to Single-Ended Output GaN RF-DAC for RF-Signal Generation. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 1646-1653.	4.6	1
15	A GaN-Based Active Diode Circuit for Low-Loss Rectification. , 2021, , .		1
16	Polarization induced interface and electron sheet charges of pseudomorphic ScAlN/GaN, GaAlN/GaN, InAlN/GaN, and InAlN/InN heterostructures. Journal of Applied Physics, 2021, 129, .	2.5	30
17	Quality Assessment of In Situ Plasma-Etched Diamond Surfaces for Chemical Vapor Deposition Overgrowth. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100035.	1.8	1
18	Investigation of GaN-on-Si and GaN-on-SOI Substrate Capacitances for Discrete and Monolithic Half-Bridges. , 2021, , .		2

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19	On the exceptional temperature stability of ferroelectric Al _{1-x} Sc _x N thin films. Applied Physics Letters, 2021, 118, .	3.3	41
20	Wurtzite ScAlN, InAlN, and GaAlN crystals, a comparison of structural, elastic, dielectric, and piezoelectric properties. Journal of Applied Physics, 2021, 130, .	2.5	40
21	A 50-nm Gate-Length Metamorphic HEMT Technology Optimized for Cryogenic Ultra-Low-Noise Operation. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 3896-3907.	4.6	17
22	Broadband 400-GHz InGaAs mHEMT Transmitter and Receiver S-MMICs. IEEE Transactions on Terahertz Science and Technology, 2021, 11, 660-675.	3.1	10
23	Atomic scale confirmation of ferroelectric polarization inversion in wurtzite-type AlScN. Journal of Applied Physics, 2021, 129, .	2.5	46
24	Properties of higher-order surface acoustic wave modes in Al _{1-x} Sc _x N/sapphire structures. Journal of Applied Physics, 2021, 130, .	2.5	8
25	Building Blocks for GaN Power Integration. IEEE Access, 2021, 9, 163122-163137.	4.2	13
26	Metal-Organic Chemical Vapor Deposition of Aluminum Scandium Nitride. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900535.	2.4	54
27	Optimization of Metal-Organic Chemical Vapor Deposition Regrown n-GaN. Physica Status Solidi (B): Basic Research, 2020, 257, 1900436.	1.5	6
28	Microstructural and optical emission properties of diamond multiply twinned particles. Journal of Applied Physics, 2020, 127, 025303.	2.5	4
29	A 600V p-GaN Gate HEMT with Intrinsic Freewheeling Schottky-Diode in a GaN Power IC with Bootstrapped Driver and Sensors. , 2020, , .		3
30	Noise Performance of Sub-100-nm Metamorphic HEMT Technologies. , 2020, , .		6
31	A Fully-Integrated W-Band I/Q-Down-Conversion MMIC for Use in Radio Astronomical Multi-Pixel Receivers. , 2020, , .		4
32	A GaN-based Current Sense Amplifier for GaN HEMTs with Integrated Current Shunts. , 2020, , .		5
33	Si-Substrate Removal for AlGaN/GaN Devices on PCB Carriers. , 2020, , .		3
34	In-Plane Oriented Stacks of c-AlScN/Mo (110) for BAW Resonators Grown by Magnetron Sputter Epitaxy. , 2020, , .		1
35	A Novel 32-Gb/s 5.6-Vpp Digital-to-Analog Converter in 100 nm GaN Technology for 5G Signal Generation. , 2020, , .		1
36	Metalorganic chemical vapor phase deposition of AlScN/GaN heterostructures. Journal of Applied Physics, 2020, 127, .	2.5	34

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37	Large-Area Lateral AlGaIn/GaN-on-Si Field-Effect Rectifier With Low Turn-On Voltage. IEEE Electron Device Letters, 2020, 41, 993-996.	3.9	20
38	Enhanced electromechanical coupling in SAW resonators based on sputtered non-polar Al _{0.77} Sc _{0.23} N 112Å ⁻¹ thin films. Applied Physics Letters, 2020, 116, .	3.3	28
39	Low-Loss Millimeter-Wave SPDT Switch MMICs in a Metamorphic HEMT Technology. IEEE Microwave and Wireless Components Letters, 2020, 30, 197-200.	3.2	17
40	Epitaxial growth of GaN/Ga ₂ O ₃ and Ga ₂ O ₃ /GaN heterostructures for novel high electron mobility transistors. Journal of Crystal Growth, 2020, 534, 125511.	1.5	35
41	Influence of Different Surface Morphologies on the Performance of High-Voltage, Low-Resistance Diamond Schottky Diodes. IEEE Transactions on Electron Devices, 2020, 67, 2471-2477.	3.0	12
42	Novel Method for Extracting Material Constants of Epitaxial Wurtzite AlScN Films on Sapphire Using Higher Order Surface Acoustic Wave Modes. , 2020, , .		2
43	Experimental determination of the electro-acoustic properties of thin film AlScN using surface acoustic wave resonators. Journal of Applied Physics, 2019, 126, .	2.5	65
44	Optical constants and band gap of wurtzite Al _{1-x} Sc _x N/Al ₂ O ₃ prepared by magnetron sputter epitaxy for scandium concentrations up to x=0.41. Journal of Applied Physics, 2019, 126, .	2.5	46
45	RF-Noise Model Extraction Procedure for Distributed Multiport Models. , 2019, , .		1
46	Integrated 2-b Riemann Pump RF-DAC in GaN Technology for 5G Base Stations. , 2019, , .		4
47	Integrated Current Sensing in GaN Power ICs. , 2019, , .		11
48	W-Band LNA MMICs Based on a Noise-Optimized 50-nm Gate-Length Metamorphic HEMT Technology. , 2019, , .		17
49	High-Q Anti-Series AlGaIn/GaN High Electron-Mobility Varactor. , 2019, , .		3
50	D-Band and G-Band High-Performance GaN Power Amplifier MMICs. IEEE Transactions on Microwave Theory and Techniques, 2019, 67, 5080-5089.	4.6	43
51	Determination of the graphene-graphite ratio of graphene powder by Raman 2D band symmetry analysis. Analytical Methods, 2019, 11, 1224-1228.	2.7	101
52	Large-Signal Modeling of a Scalable High- Q AlGaIn/GaN High Electron-Mobility Varactor. IEEE Transactions on Microwave Theory and Techniques, 2019, 67, 922-927.	4.6	4
53	Investigation of growth parameters for ScAlN-barrier HEMT structures by plasma-assisted MBE. Japanese Journal of Applied Physics, 2019, 58, SC1045.	1.5	42
54	Epitaxial growth optimization of AlGaIn/GaN high electron mobility transistor structures on 3C-SiC/Si. Journal of Applied Physics, 2019, 125, .	2.5	15

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55	AlGaN avalanche Schottky diodes with high Al-content. Japanese Journal of Applied Physics, 2019, 58, SCCC11.	1.5	10
56	A Transmitter System-in-Package at 300 GHz With an Off-Chip Antenna and GaAs-Based MMICs. IEEE Transactions on Terahertz Science and Technology, 2019, 9, 335-344.	3.1	22
57	Highly Scalable Distributed High Electron Mobility Transistor Model. , 2019, , .		3
58	Asymmetrical Substrate-Biasing Effects at up to 350V Operation of Symmetrical Monolithic Normally-Off GaN-on-Si Half-Bridges. , 2019, , .		5
59	A Pseudo-Complementary GaN-Based Gate Driver with Reduced Static Losses. , 2019, , .		3
60	High voltage electrochemical exfoliation of graphite for high-yield graphene production. RSC Advances, 2019, 9, 29305-29311.	3.6	19
61	Experimental determination of Al _{1-x} Sc _x N thin film thermo-electro-acoustic properties up to 140Â°C by using SAW resonators. , 2019, , .		0
62	GCPW GaAs Broadside Couplers at H-Band and Application to Balanced Power Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2019, 67, 78-85.	4.6	7
63	Temperature Dependence of the Pyroelectric Coefficient of AlScN Thin Films. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700831.	1.8	24
64	Broadband High-Power W-Band Amplifier MMICs Based on Stacked-HEMT Unit Cells. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 1312-1318.	4.6	29
65	Avalanche multiplication in AlGaN-based heterostructures for the ultraviolet spectral range. Applied Physics Letters, 2018, 112, .	3.3	17
66	Highly Isolating and Broadband Single-Pole Double-Throw Switches for Millimeter-Wave Applications Up to 330 GHz. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 1998-2009.	4.6	29
67	Graphene as an active virtually massless top electrode for RF solidly mounted bulk acoustic wave (SMR-BAW) resonators. Nanotechnology, 2018, 29, 105302.	2.6	12
68	Analysis and Development of Submillimeter-Wave Stacked-FET Power Amplifier MMICs in 35-nm mHEMT Technology. IEEE Transactions on Terahertz Science and Technology, 2018, 8, 357-364.	3.1	14
69	W-band SPDT switches in planar and tri-gate 100-nm gate-length GaN-HEMT technology. , 2018, , .		20
70	Voltage- and Temperature-Dependent Degradation of AlN/GaN High Electron Mobility Transistors. , 2018, , .		3
71	Multi-Stage Cascode in High-Voltage AlGaN/GaN-on-Si Technology. , 2018, , .		6
72	Full W-Band GaN Power Amplifier MMICs Using a Novel Type of Broadband Radial Stub. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 5664-5675.	4.6	19

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73	Determination of Elastic and Piezoelectric Properties of $\text{Al}_{0.84}\text{Sc}_{0.16}\text{N}$ Thin Films. , 2018, , .		2
74	Instabilities by Parasitic Substrate-Loop of GaN-on-Si HEMTs in Half-Bridges. , 2018, , .		1
75	Riemann-Pump based RF-Power DACs in GaN Technology for 5G Base Stations. , 2018, , .		5
76	A G_{S} -Band Broadband Balanced Power Amplifier Module Based on Cascode mHEMTs. IEEE Microwave and Wireless Components Letters, 2018, 28, 924-926.	3.2	7
77	Investigations of Active Antenna Doherty Power Amplifier Modules Under Beam-Steering Mismatch. IEEE Microwave and Wireless Components Letters, 2018, 28, 930-932.	3.2	10
78	Monolithically integrated power circuits in high-voltage GaN-on-Si heterojunction technology. IET Power Electronics, 2018, 11, 681-688.	2.1	35
79	Transfer of AlGaIn/GaN RF-devices onto diamond substrates via van der Waals bonding. International Journal of Microwave and Wireless Technologies, 2018, 10, 666-673.	1.9	20
80	Elastic modulus and coefficient of thermal expansion of piezoelectric $\text{Al}_{1-x}\text{Sc}_x\text{N}$ (up to $x = 0.41$) thin films. APL Materials, 2018, 6, 076105.	5.1	71
81	Temperature Cross-Sensitivity of AlN-Based Flexural Plate Wave Sensors. IEEE Sensors Journal, 2018, 18, 7810-7818.	4.7	4
82	A 300 GHz microstrip multilayered antenna on quartz substrate. , 2018, , .		7
83	W_{S} -Band Time-Domain Multiplexing FMCW MIMO Radar for Far-Field 3-D Imaging. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 3474-3484.	4.6	105
84	Microstructure and mechanical properties of stress-tailored piezoelectric AlN thin films for electro-acoustic devices. Applied Surface Science, 2017, 407, 307-314.	6.1	34
85	Nanodiamond resonators fabricated on $8\text{-}\mu\text{m}^3$ Si substrates using adhesive wafer bonding. Journal of Micromechanics and Microengineering, 2017, 27, 065011.	2.6	2
86	Reliability Analysis of LPCVD SiN Gate Dielectric for AlGaIn/GaN MIS-HEMTs. IEEE Transactions on Electron Devices, 2017, 64, 2298-2305.	3.0	28
87	Development of a Silicon-Only Capacitive Dew Point Sensor. IEEE Sensors Journal, 2017, 17, 7223-7230.	4.7	5
88	AlN/GaN HEMTs grown by MBE and MOCVD: Impact of Al distribution. Physica Status Solidi (B): Basic Research, 2017, 254, 1600715.	1.5	23
89	Design, Realization, and Evaluation of a Riemann Pump in GaN Technology. IEEE Microwave and Wireless Components Letters, 2017, 27, 672-674.	3.2	6
90	Substrate biasing effects in a high-voltage, monolithically-integrated half-bridge GaN-Chip. , 2017, , .		25

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91	Effect of substrate termination on switching loss and switching time using 600 V GaN-on-Si HEMTs with integrated gate driver in half-bridges. , 2017, , .		13
92	Operation of PCB-embedded, high-voltage multilevel-converter GaN-IC. , 2017, , .		11
93	Wettability Investigations and Wet Transfer Enhancement of Large-Area CVD-Graphene on Aluminum Nitride. Nanomaterials, 2017, 7, 226.	4.1	7
94	Electrostatic Self-Assembly of Diamond Nanoparticles onto Al- and N-Polar Sputtered Aluminum Nitride Surfaces. Nanomaterials, 2016, 6, 217.	4.1	10
95	Quasi-Bessel beams from asymmetric and astigmatic illumination sources. Optics Express, 2016, 24, 17433.	3.4	9
96	Piezoelectric AlN Films for FPW Sensors with Improved Device Performance. Procedia Engineering, 2016, 168, 1040-1043.	1.2	3
97	Compact W-band receiver module on hybrid liquid crystal polymer board. , 2016, , .		4
98	Single-input GaN gate driver based on depletion-mode logic integrated with a 600 V GaN-on-Si power transistor. , 2016, , .		10
99	Soft-switching 3 MHz converter based on monolithically integrated half-bridge GaN-chip. , 2016, , .		18
100	Enhanced actuation of nanocrystalline diamond microelectromechanical disk resonators with AlN layers. Applied Physics Letters, 2016, 108, .	3.3	9
101	Analysis and optimization of sputter deposited AlN-layers for flexural plate wave devices. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, .	1.2	18
102	Piezo-force and Vibration Analysis of ZnO Nanowire Arrays for Sensor Application. Procedia Engineering, 2016, 168, 1192-1195.	1.2	9
103	Study of a silicon parallel plate capacitor as a dew point sensor. , 2016, , .		4
104	Measurement setup for the analysis of broadband frequency-modulated signals. , 2016, , .		0
105	Material characterization using a compact W-band ellipsometer. , 2016, , .		1
106	A W-band wireless communication transmitter utilizing a stacked-FET oscillator for high output power performance. , 2016, , .		3
107	An investigation of millimeter wave switches based on shunt transistors including SPDT SWITCH MMICs up to 300 GHz. , 2016, , .		8
108	Post drain-stress behavior of AlGaIn/GaN-on-Si MIS-HEMTs. Solid-State Electronics, 2016, 125, 125-132.	1.4	0

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109	Small signal modelling approach for submillimeter wave III-V HEMTs with analysis and optimization possibilities. , 2016, , .		13
110	RF Performance of Trigate GaN HEMTs. IEEE Transactions on Electron Devices, 2016, 63, 4255-4261.	3.0	18
111	Stability Investigation of Large Gate-Width Metamorphic High Electron-Mobility Transistors at Cryogenic Temperature. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 3139-3150.	4.6	16
112	Spectroscopic Measurement of Material Properties Using an Improved Millimeter-Wave Ellipsometer Based on Metallic Substrates. IEEE Transactions on Instrumentation and Measurement, 2016, 65, 2551-2559.	4.7	5
113	Low noise amplifiers for MetOp-SG. , 2016, , .		5
114	Complex interaction of passive multiport structures and their description by separate discrete models. Electronics Letters, 2016, 52, 52-54.	1.0	1
115	Linear temperature sensors in high-voltage GaN-HEMT power devices. , 2016, , .		9
116	The role of surface electron accumulation and bulk doping for gas-sensing explored with single-crystalline In ₂ O ₃ thin films. Sensors and Actuators B: Chemical, 2016, 236, 909-916.	7.8	41
117	Prospects and Limitations of Stacked-FET Approaches for Enhanced Output Power in Voltage-Controlled Oscillators. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 836-846.	4.6	13
118	Pinhole-free ultra-thin nanocrystalline diamond film growth via electrostatic self-assembly seeding with increased salt concentration of nanodiamond colloids. Diamond and Related Materials, 2016, 63, 103-107.	3.9	16
119	Admittance-voltage profiling of Al _x Ga _{1-x} N/GaN heterostructures: Frequency dependence of capacitance and conductance. Journal of Applied Physics, 2015, 118, .	2.5	4
120	Large area InN terahertz emitters based on the lateral photo-Dember effect. Applied Physics Letters, 2015, 107, .	3.3	7
121	Characterization of quasi-optical focusing systems at W-band frequencies. , 2015, , .		3
122	Dynamic Detection of Target-DNA with AlGaIn/GaN High Electron Mobility Transistors. Procedia Engineering, 2015, 120, 908-911.	1.2	3
123	Monolithic integrated quasi-normally-off gate driver and 600 V GaN-on-Si HEMT. , 2015, , .		20
124	Impact of Metallization Layer Structure on the Performance of G-Band Branch-Line Couplers. IEEE Microwave and Wireless Components Letters, 2015, 25, 793-795.	3.2	3
125	Impedance Characterization of DNA-functionalization Layers on AlGaIn/GaN High Electron Mobility Transistors. Procedia Engineering, 2015, 120, 912-915.	1.2	3
126	A compact W-band LFM CW radar module with high accuracy and integrated signal processing. , 2015, , .		17

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127	Monolithic three-stage 6â€“18GHz high power amplifier with distributed interstage in GaN technology. , 2015, , .		7
128	Detection of different target-DNA concentrations with highly sensitive AlGaIn/GaN high electron mobility transistors. Sensors and Actuators B: Chemical, 2015, 210, 633-639.	7.8	27
129	Threshold Voltage Engineering in GaN-Based HFETs: A Systematic Study With the Threshold Voltage Reaching More Than 2 V. IEEE Transactions on Electron Devices, 2015, 62, 538-545.	3.0	23
130	High-voltage stress time-dependent dispersion effects in AlGaIn/GaN HEMTs. , 2015, , .		6
131	Integrated reverse-diodes for GaN-HEMT structures. , 2015, , .		26
132	Quasi-normally-off GaN gate driver for high slew-rate d-mode GaN-on-Si HEMTs. , 2015, , .		6
133	Charge balancing in GaN-based 2-D electron gas devices employing an additional 2-D hole gas and its influence on dynamic behaviour of GaN-based heterostructure field effect transistors. Journal of Applied Physics, 2015, 117, .	2.5	21
134	Appropriate Salt Concentration of Nanodiamond Colloids for Electrostatic Self-Assembly Seeding of Monosized Individual Diamond Nanoparticles on Silicon Dioxide Surfaces. Langmuir, 2015, 31, 5319-5325.	3.5	50
135	High-Efficiency, High-Temperature Continuous Class-E Sub-Waveform Solution AlGaIn/GaN Power Amplifier. IEEE Microwave and Wireless Components Letters, 2015, 25, 526-528.	3.2	7
136	Normally-Off AlGaIn/GaN/AlGaIn Double Heterostructure FETs With a Thick Undoped GaN Gate Layer. IEEE Electron Device Letters, 2015, 36, 905-907.	3.9	16
137	Vertical Buffer Leakage and Temperature Effects on the Breakdown Performance of GaN/AlGaIn HEMTs on Si Substrate. ECS Transactions, 2015, 69, 65-70.	0.5	5
138	A 183 GHz Metamorphic HEMT Low-Noise Amplifier With 3.5 dB Noise Figure. IEEE Microwave and Wireless Components Letters, 2015, 25, 618-620.	3.2	31
139	On the Accurate Measurement and Calibration of S-Parameters for Millimeter Wavelengths and Beyond. IEEE Transactions on Microwave Theory and Techniques, 2015, 63, 2335-2342.	4.6	30
140	Monolithically-Integrated Multilevel Inverter on Lateral GaN-on-Si Technology for High-Voltage Applications. , 2015, , .		6
141	Electrochemical generation of hydrogenated graphene flakes. Carbon, 2015, 83, 128-135.	10.3	49
142	Investigation of dielectric properties of multilayer structures consisting of homogeneous plastics and liquid solutions at 75â€“110 GHz. Journal of Sensors and Sensor Systems, 2015, 4, 125-131.	0.9	2
143	Nano-diamond based spheres for radio frequency electromechanical resonators. Journal of Micromechanics and Microengineering, 2014, 24, 045015.	2.6	3
144	Realization of a 30-W highly efficient and linear reconfigurable dual-band power amplifier using the continuous mode approach. International Journal of Microwave and Wireless Technologies, 2014, 6, 115-128.	1.9	7

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145	243 GHz low-noise amplifier MMICs and modules based on metamorphic HEMT technology. International Journal of Microwave and Wireless Technologies, 2014, 6, 215-223.	1.9	15
146	Reliability of GaN HEMTs with a 100 nm gate length under DC-stress tests. , 2014, , .		4
147	Planar Zero Bias Schottky Diodes on an InGaAs Metamorphic HEMT MMIC Process. IEEE Microwave and Wireless Components Letters, 2014, 24, 860-862.	3.2	6
148	Influence of surface states on the voltage robustness of AlGaIn/GaN HFET power devices. Microelectronics Reliability, 2014, 54, 2656-2661.	1.7	9
149	Combining external cavity quantum cascade lasers and MOEMS technology: An approach for miniaturization and fast wavelength scanning. , 2014, , .		0
150	Elastic properties of ultrathin diamond/AlN membranes. Thin Solid Films, 2014, 558, 267-271.	1.8	10
151	Excitons and exciton-phonon coupling in the optical response of GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 297-301.	0.8	4
152	A scalable compact small-signal mHEMT model accounting for distributed effects in sub-millimeter wave and terahertz applications. , 2014, , .		6
153	Improved AlGaIn p-i-n Photodetectors for Monitoring of Ultraviolet Radiation. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 166-172.	2.9	22
154	Processing of Nanoscale Gaps for Boron-doped Nanocrystalline Diamond Based MEMS. Procedia Engineering, 2014, 87, 903-906.	1.2	2
155	Functional Nanowires: Synthesis, Characterization and Applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 313-314.	0.8	0
156	Electroluminescence Investigation of the Lateral Field Distribution in AlGaIn/GaN HEMTs for Power Applications. Acta Physica Polonica A, 2014, 125, 982-985.	0.5	3
157	CIP (cleaning-in-place) stability of AlGaIn/GaN pH sensors. Journal of Biotechnology, 2013, 163, 354-361.	3.8	10
158	Piezoelectric actuated micro-resonators based on the growth of diamond on aluminum nitride thin films. Nanotechnology, 2013, 24, 025601.	2.6	46
159	High-Gain Millimeter-Wave AlGaIn/GaN Transistors. IEEE Transactions on Electron Devices, 2013, 60, 3112-3118.	3.0	16
160	Enhanced mechanical performance of AlN/nanodiamond micro-resonators. Journal of Micromechanics and Microengineering, 2013, 23, 125017.	2.6	18
161	Wireless sub-THz communication system with high data rate. Nature Photonics, 2013, 7, 977-981.	31.4	1,137
162	Sub-10 nanometer uncooled platinum bolometers via plasma enhanced atomic layer deposition. , 2013, , .		9

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163	Novel semi-reactively-matched multistage broadband power amplifier architecture for monolithic ICs in GaN technology. , 2013, , .		8
164	Transparent diamond electrodes for tunable micro-optical devices. Diamond and Related Materials, 2013, 38, 101-103.	3.9	10
165	Benchmarking of Large-Area GaN-on-Si HFET Power Devices for Highly-Efficient, Fast-Switching Converter Applications. , 2013, , .		9
166	GaN-based high voltage transistors for efficient power switching. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 831-834.	0.8	33
167	Thermal Functionalization of GaN Surfaces with 1-Alkenes. Langmuir, 2013, 29, 6296-6301.	3.5	11
168	Piezoelectrically actuated diamond cantilevers for high-frequency applications. Diamond and Related Materials, 2013, 38, 69-72.	3.9	0
169	Corrugated piezoelectric membranes for energy harvesting from aperiodic vibrations. Sensors and Actuators A: Physical, 2013, 195, 32-37.	4.1	7
170	A 67 GHz GaN Voltage-Controlled Oscillator MMIC With High Output Power. IEEE Microwave and Wireless Components Letters, 2013, 23, 374-376.	3.2	16
171	Seebeck ozone sensors. , 2013, , .		1
172	Dynamics of thermalization in GaInN/GaN quantum wells grown on ammonothermal GaN. Journal of Applied Physics, 2013, 114, .	2.5	14
173	A 243 GHz LNA Module Based on mHEMT MMICs With Integrated Waveguide Transitions. IEEE Microwave and Wireless Components Letters, 2013, 23, 486-488.	3.2	22
174	Mechanical and electrical properties of plasma and thermal atomic layer deposited Al ₂ O ₃ films on GaAs and Si. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	16
175	Crystallographic Texture of Submicron Thin Aluminum Nitride Films on Molybdenum Electrode for Suspended Micro and Nanosystems. ECS Journal of Solid State Science and Technology, 2013, 2, P180-P184.	1.8	2
176	W-band active loads and switching front-end MMICs for radiometer calibration. International Journal of Microwave and Wireless Technologies, 2013, 5, 293-299.	1.9	1
177	Microscopic Degradation Analysis of RF-Stressed AlGaIn/GaN HEMTs. Materials Science Forum, 2012, 725, 79-82.	0.3	2
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